

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

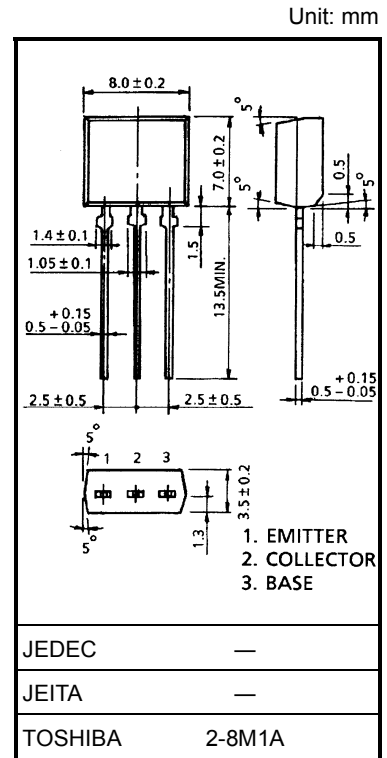
2SC5154

Power Amplifier Applications
 Driver Stage Amplifier Applications

- High transition frequency: $f_T = 100$ MHz (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	160	V
Collector-emitter voltage		V_{CEO}	160	V
Emitter-base voltage		V_{EBO}	5	V
Collector current	DC	I_C	1.5	A
	Pulse	I_{CP}	3.0	
Base current		I_B	0.15	A
Collector power dissipation		P_C	1.3	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-50 to 150	°C



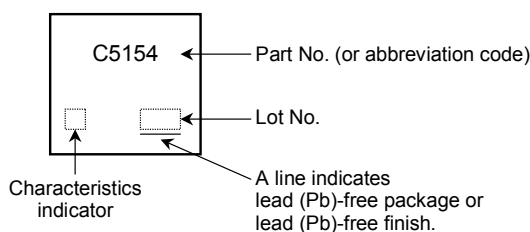
Weight: 0.55 g (typ.)

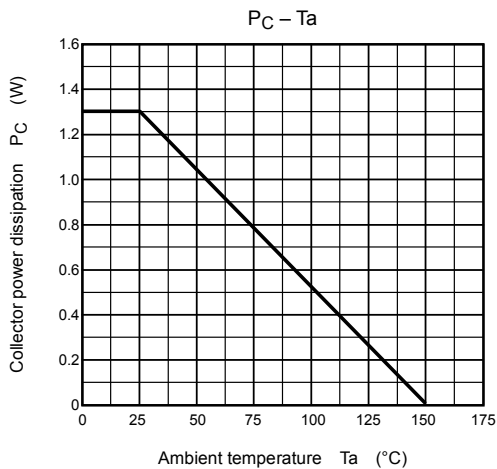
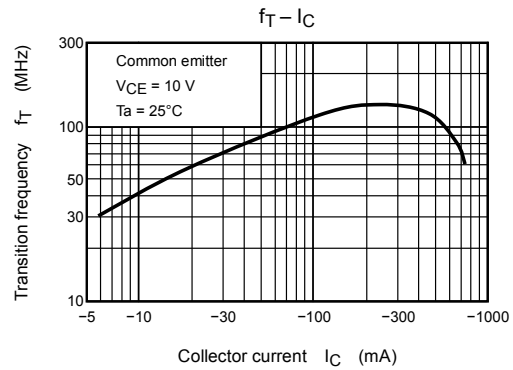
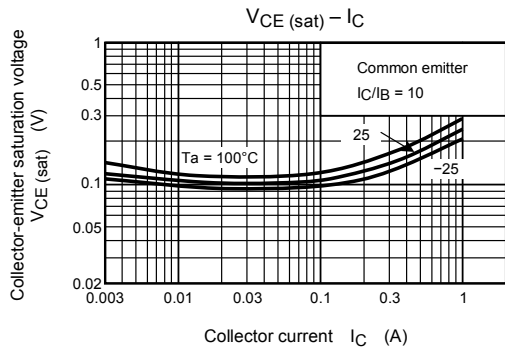
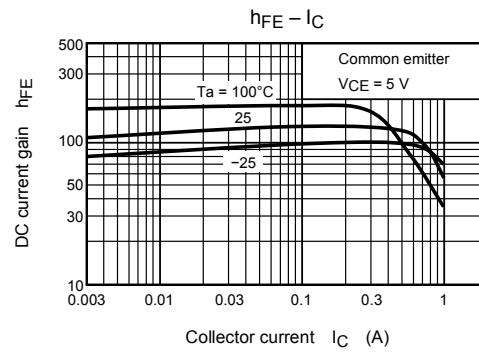
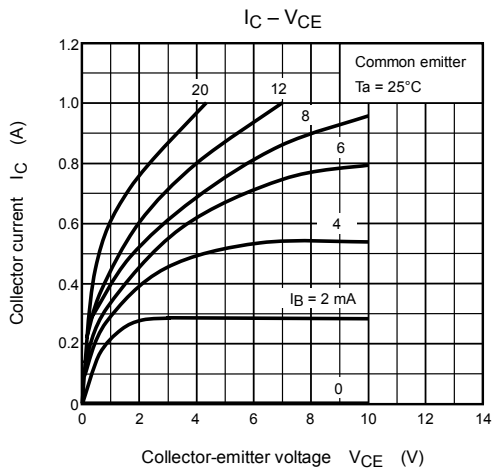
Electrical Characteristics (Ta = 25°C)

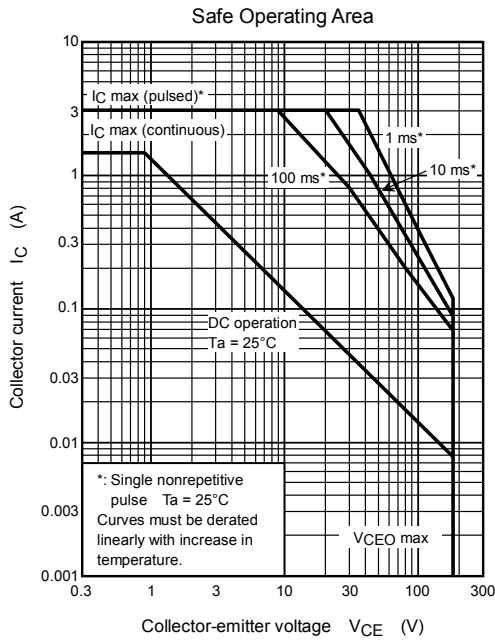
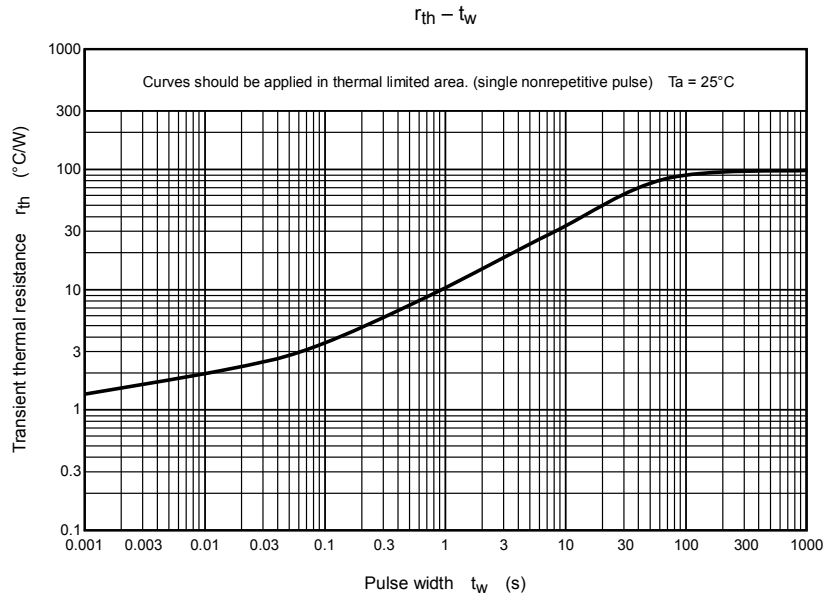
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 160$ V, $I_E = 0$	—	—	1.0	μ A
Emitter cut-off current	I_{EBO}	$V_{EB} = 5$ V, $I_C = 0$	—	—	1.0	μ A
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10$ mA, $I_B = 0$	160	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = 5$ V, $I_C = 100$ mA	70	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500$ mA, $I_B = 50$ mA	—	—	1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = 5$ V, $I_C = 500$ mA	—	0.75	0.95	V
Transition frequency	f_T	$V_{CE} = 10$ V, $I_C = 100$ mA	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10$ V, $I_C = 0$, $f = 1$ MHz	—	25	—	pF

Note: h_{FE} classification O: 70 to 140, Y: 120 to 240

Marking







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